INSTRUMENT: HALL PROBE (Ge Crystal) # 6374

Specification of the material

Crystal	:	n-type lightly doped
Hall Coefficient	:	21.0×10^3 cm^3 $Coulomb^{-1}$
Carrier Mobility	:	35.0×10^2 cm^2. $Volt^{-1}$. sec^{-1}
Carrier density	:	3.0×10^{14} cm^{-3}
Resistivity	:	$\cong$ 6 ohm. cm.

Details of the Hall Probe

Length & Width	:	The distance between the respective probes
Thickness	:	0.50 mm
Maximum Current	:	10 mA
Input Current Leads	:	Red & Black
Hall Voltage Output Leads	:	Yellow & Green

Test Parameters

Input Current	:	8.00 mA
Offset Voltage	:	< 1.0 mV
Hall Voltage	:	33.6 mV/8.0 mA/KG

**Measured by. Digital Hall Effect Set-up, DHE-21*

Passed for despatch: Yes **Dated:** 11.11.2014

Q.C. Engineer: U.S. Chauhan

INSTRUMENT : HALL PROBE (Ge Crystal) # 6351

Specification of the Material

Crystal	:	p-type lightly doped
Hall Coefficient	:	19.7×10^3 cm^3 $Coulomb^{-1}$
Carrier Mobility	:	28.1×10^2 cm^2. $Volt^{-1}$. sec^{-1}
Carrier density	:	3.2×10^{14} cm^{-3}
Resistivity	:	$\cong$ 7 ohm. cm.

Details of the Hall Probe

Length & Width	:	The distance between the respective probes
Thickness	:	0.50 mm
Maximum Cuurrent	:	10 mA
Input Current Leads	:	Red & Black
Hall Voltage Output Leads	:	Yellow & Green

Test Parameters

Input Current	:	8.00 mA
Offset Voltage	:	< 1.0 mV
Hall Voltage	:	31.5 mV/8.0 mA/KG

**Measured by. Digital Hall Effect Set-up, DHE-21*

Passed for dispatch : Yes **Dated :** 08.11.2014

Q.C. Engineer: U.S. Chauhan